Abstracts

Optimized 0.1 µm GaAs MESFET's

K. Moore, J. East, G. Haddad and T. Brock. "Optimized 0.1 µm GaAs MESFET's." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 643-646.

We have optimized the design of conventional GaAs MESFET's for high frequency operation. FET's were fabricated using electron beam lithography to define 0.1 µm "mushroom" and "Gamma" gates. The best results obtained include peak transconductance of 600mS/mm, f/sub t/ = 93 GHz, and f/sub max/ >= 150 GHz. In addition, studies were carried out to examine the effect of gate shape and location on high frequency device performance.

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